1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in an ultra small SOT666 Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Logic-level compatible
- Very fast switching
- · Trench MOSFET technology
- AEC-Q101 qualified

3. Applications

- Relay driver
- · High-speed line driver
- Low-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-------------------|----------------------------------|--|-----|-----|-----|-----|------|
| Per transistor | | | | | • | | |
| V _{DS} | drain-source voltage | T _{amb} = 25 °C | | - | - | 60 | V |
| V_{GS} | gate-source voltage | | | -20 | - | 20 | V |
| I _D | drain current | V _{GS} = 10 V; T _{amb} = 25 °C | [1] | - | - | 350 | mA |
| Static charact | eristics (per transistor) | | | | | | |
| R _{DSon} | drain-source on-state resistance | V_{GS} = 10 V; I_D = 500 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.01; T_j = 25 °C | | - | 1 | 1.6 | Ω |

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--------------------|----------------|
| 1 | S1 | source1 | 6 5 4 | D1 D2 |
| 2 | G1 | gate1 | | |
| 3 | D2 | drain2 | | |
| 4 | S2 | source2 | | |
| 5 | G2 | gate2 | 1 2 3 | |
| 6 | D1 | drain1 | SOT666 | 017aaa254 |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | | |
|-------------|---------|---|---------|--|--|--|
| | Name | Description | Version | | | |
| 2N7002PV | SOT666 | plastic, surface-mounted package; 6 leads; 0.5 mm pitch; 1.6 mm x 1.2 mm x 0.55 mm body | SOT666 | | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| 2N7002PV | ZF |

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|--|--|-----|-----|------|------|
| Per transiste | or | | | | | |
| V _{DS} | drain-source voltage | T _{amb} = 25 °C | | - | 60 | V |
| V_{GS} | gate-source voltage | | | -20 | 20 | V |
| I _D | drain current | V _{GS} = 10 V; T _{amb} = 25 °C | [1] | - | 350 | mA |
| | | V _{GS} = 10 V; T _{amb} = 100 °C | [1] | - | 250 | mA |
| I _{DM} | peak drain current | T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs | | - | 1.2 | Α |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | [2] | - | 330 | mW |
| | | | [1] | - | 390 | mW |
| | | T _{sp} = 25 °C | | - | 1090 | mW |
| Per device | | | | | | _ |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | [2] | - | 500 | mW |
| T _j | junction temperature | | | - | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |
| Source-drain | n diode | | ' | 1 | | |
| I _S | source current | T _{amb} = 25 °C | [1] | - | 350 | mA |
| | The state of the s | The state of the s | | | | |

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

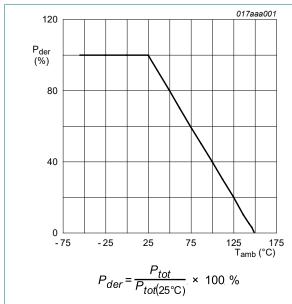


Fig. 1. Normalized total power dissipation as a function of ambient temperature

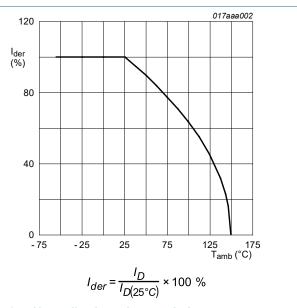
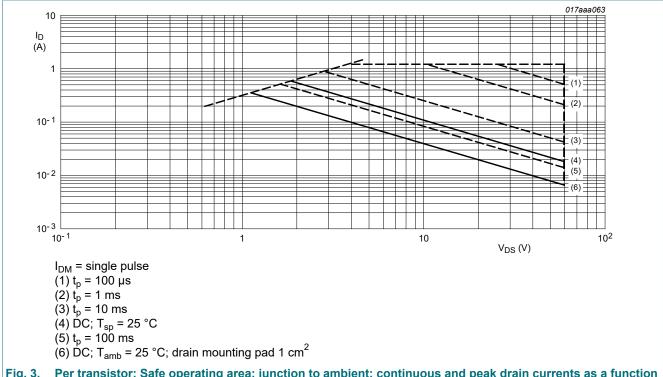


Fig. 2. Normalized continuous drain current as a function of ambient temperature

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60 V, 350 mA dual N-channel Trench MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-----------------------|--|-------------|-----|-----|-----|-----|------|
| Per device | | | | | | | |
| R _{th(j-a)} | thermal resistance from junction to ambient | in free air | [1] | - | - | 250 | K/W |
| Per transist | or | | | | | | |
| R _{th(j-a)} | thermal resistance from | in free air | [1] | - | 330 | 380 | K/W |
| | junction to ambient | | [2] | - | 280 | 320 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | - | 115 | K/W |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

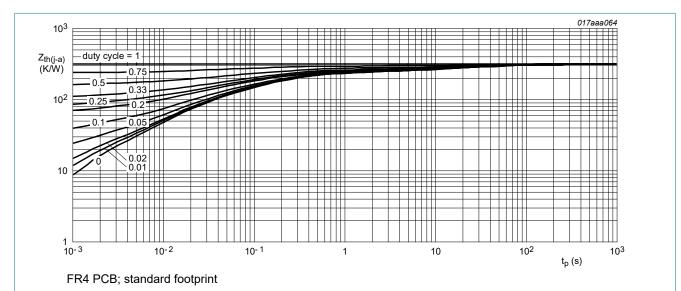


Fig. 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

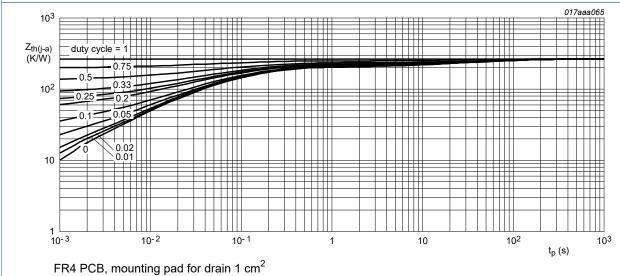


Fig. 5. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

2N7002PV

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10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|-----------------------------------|--|------|------|------|------|
| Static chara | acteristics (per transistor) | | | | | |
| V _{(BR)DSS} | drain-source breakdown voltage | $I_D = 10 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ | 60 | - | - | V |
| V_{GSth} | gate-source threshold voltage | $I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$ | 1.1 | 1.75 | 2.4 | V |
| I _{DSS} | drain leakage current | V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C | - | - | 1 | μΑ |
| | | V _{DS} = 60 V; V _{GS} = 0 V; T _j = 150 °C | - | - | 10 | μΑ |
| I _{GSS} | gate leakage current | V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 100 | nA |
| | | $V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | - | -100 | nA |
| R _{DSon} | drain-source on-state resistance | V_{GS} = 5 V; I_{D} = 50 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.01; T_{j} = 25 °C | - | 1.3 | 2 | Ω |
| | | V_{GS} = 10 V; I_{D} = 500 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.01; T_{j} = 25 °C | - | 1 | 1.6 | Ω |
| 9 _{fs} | forward transconductance | V_{DS} = 10 V; I_{D} = 200 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.01; T_{j} = 25 °C | - | 400 | - | mS |
| Dynamic ch | naracteristics (per transist | or) | | | | |
| Q _{G(tot)} | total gate charge | V _{DS} = 30 V; I _D = 300 mA; V _{GS} = 4.5 V; | - | 0.6 | 0.8 | nC |
| Q _{GS} | gate-source charge | T _j = 25 °C | - | 0.2 | - | nC |
| Q_{GD} | gate-drain charge | | - | 0.2 | - | nC |
| C _{iss} | input capacitance | V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V; | - | 30 | 50 | pF |
| C _{oss} | output capacitance | T _j = 25 °C | - | 7 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 4 | - | pF |
| t _{d(on)} | turn-on delay time | $V_{DS} = 50 \text{ V}; R_L = 250 \Omega; V_{GS} = 10 \text{ V};$ | - | 3 | 6 | ns |
| t _r | rise time | $R_{G(ext)} = 6 \Omega; T_j = 25 °C$ | - | 4 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 10 | 20 | ns |
| t _f | fall time | | - | 5 | - | ns |
| Source-dra | in diode (per transistor) | | • | | | |
| V_{SD} | source-drain voltage | I _S = 115 mA; V _{GS} = 0 V; T _j = 25 °C | 0.47 | 0.75 | 1.1 | V |

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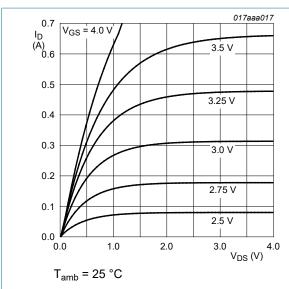
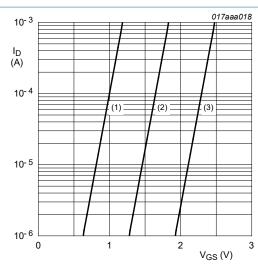


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

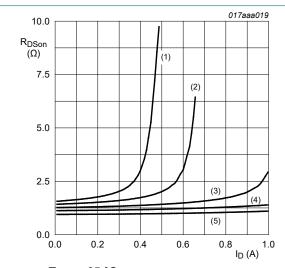


 T_{amb} = 25 °C; V_{DS} = 5 V (1) minimum values

(2) typical values

(3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage



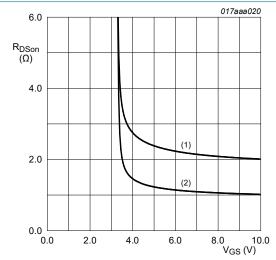
 T_{amb} = 25 °C

(1) $V_{GS} = 3.25 \text{ V}$

 $(2) V_{GS} = 3.5 V$

(3) $V_{GS} = 4 V$ (4) $V_{GS} = 5 V$ $(5) V_{GS} = 10 V$

Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



 $I_D = 500 \text{ mA}$

(1) T_{amb} = 150 °C

 $(2) T_{amb} = 25 °C$

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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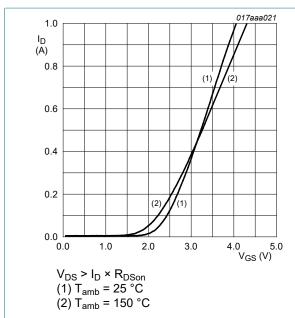
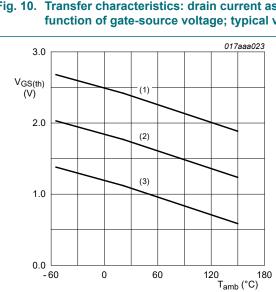


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of ambient temperature

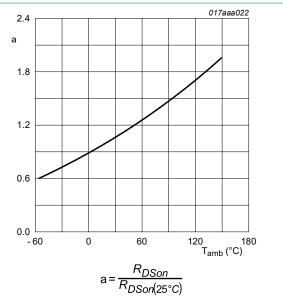
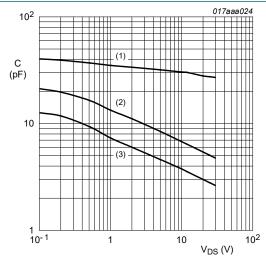


Fig. 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values



 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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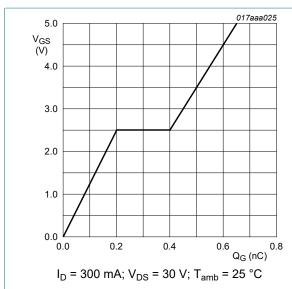


Fig. 14. Gate-source voltage as a function of gate charge; typical values

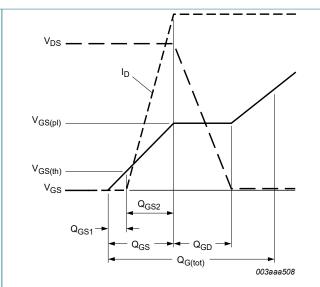
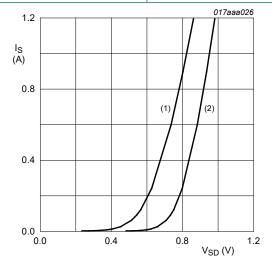


Fig. 15. Gate charge waveform definitions

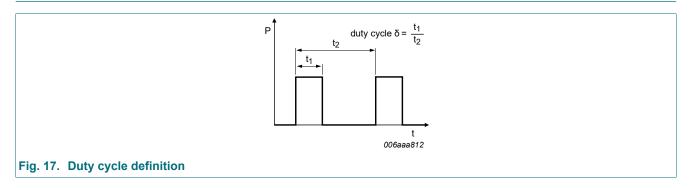


V_{GS} = 0 V (1) T_{amb} = 150 °C (2) T_{amb} = 25 °C

Fig. 16. Source current as a function of source-drain voltage; typical values

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11. Test information



Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

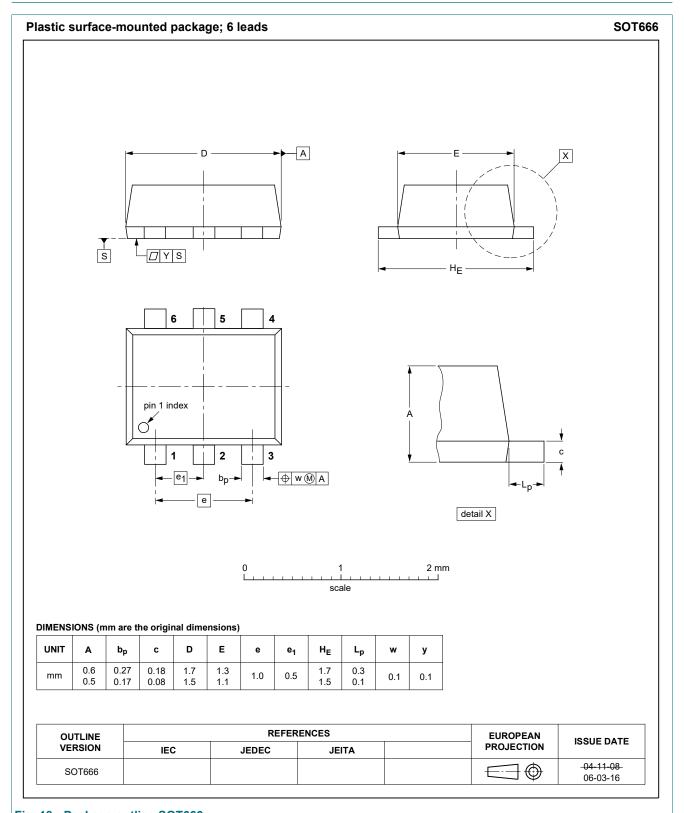
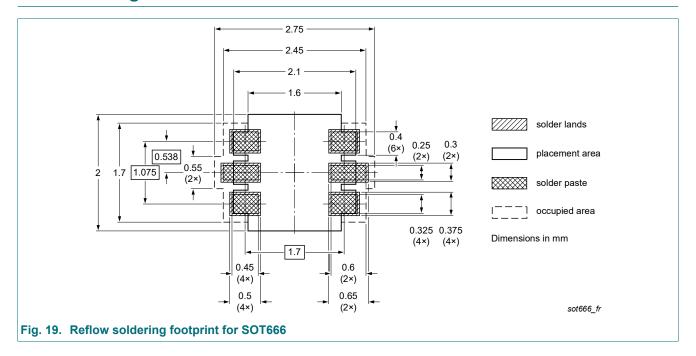


Fig. 18. Package outline SOT666

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13. Soldering



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14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes | | | | | |
|----------------|------------------------------|--|---------------|--------------|--|--|--|--|--|
| 2N7002PV v.2 | 20201123 | Product data sheet | - | 2N7002PV v.1 | | | | | |
| Modifications: | Nexperia. • Legal texts have | The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Chapter "Characteristics": Typo correction for I_{GSS} and switching times. | | | | | | | |
| 2N7002PV v.1 | 20100805 | Product data sheet | - | - | | | | | |

15. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|-----------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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